

06N60-VB TO220 Datasheet

N-Channel 600V (D-S) Power MOSFET

PRODUCT SUMMARY	
V_{DS} (V)	600
$R_{DS(on)}$ (Ω)	$V_{GS} = 10\text{ V}$ 0.780
Q_g max. (nC)	49
Q_{gs} (nC)	13
Q_{gd} (nC)	20
Configuration	Single

FEATURES

- Low gate charge Q_g results in simple drive requirement
- Improved gate, avalanche and dynamic dV/dt ruggedness
- Fully characterized capacitance and avalanche voltage and current

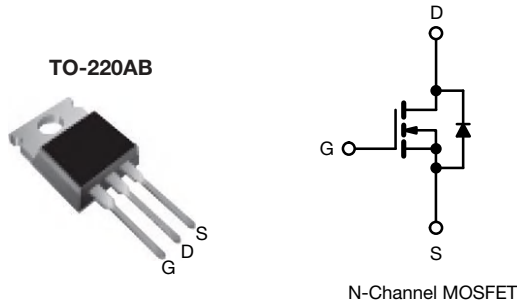


APPLICATIONS

- Switch mode power supply (SMPS)
- Uninterruptible power supply
- High speed power switching

APPLICABLE OFF LINE SMPS TOPOLOGIES

- Active clamped forward
- Main switch




ABSOLUTE MAXIMUM RATINGS ($T_C = 25\text{ }^\circ\text{C}$, unless otherwise noted)					
PARAMETER		SYMBOL	LIMIT	UNIT	
Drain-Source Voltage		V_{DS}	600	V	
Gate-Source Voltage		V_{GS}	± 30		
Continuous Drain Current	V_{GS} at 10 V	I_D	$T_C = 25\text{ }^\circ\text{C}$	8.0	A
			$T_C = 100\text{ }^\circ\text{C}$	5.8	
Pulsed Drain Current ^a		I_{DM}	37		
Linear Derating Factor			1.3	$W/^\circ\text{C}$	
Single Pulse Avalanche Energy ^b		E_{AS}	290	mJ	
Repetitive Avalanche Current ^a		I_{AR}	8.0	A	
Repetitive Avalanche Energy ^a		E_{AR}	17	mJ	
Maximum Power Dissipation	$T_C = 25\text{ }^\circ\text{C}$	P_D	170	W	
Peak Diode Recovery dV/dt ^c		dV/dt	5.0	V/ns	
Operating Junction and Storage Temperature Range		T_J, T_{stg}	-55 to +150	$^\circ\text{C}$	
Soldering Recommendations (Peak temperature) ^d	for 10 s		300		
Mounting Torque	6-32 or M3 screw		10	lbf · in	
			1.1	N · m	

Notes

- Repetitive rating; pulse width limited by maximum junction temperature (see fig. 11).
- Starting $T_J = 25\text{ }^\circ\text{C}$, $L = 6.8\text{ mH}$, $R_g = 25\text{ }^\circ\Omega$, $I_{AS} = 9.2\text{ A}$ (see fig. 12).
- $I_{SD} \leq 9.2\text{ A}$, $dI/dt \leq 50\text{ A}/\mu\text{s}$, $V_{DD} \leq V_{DS}$, $T_J \leq 150\text{ }^\circ\text{C}$.
- 1.6 mm from case.

THERMAL RESISTANCE RATINGS				
PARAMETER	SYMBOL	TYP.	MAX.	UNIT
Maximum Junction-to-Ambient	R_{thJA}	-	62	°C/W
Case-to-Sink, Flat, Greased Surface	R_{thCS}	0.50	-	
Maximum Junction-to-Case (Drain)	R_{thJC}	-	0.75	

SPECIFICATIONS ($T_J = 25\text{ }^\circ\text{C}$, unless otherwise noted)							
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNIT	
Static							
Drain-Source Breakdown Voltage	V_{DS}	$V_{GS} = 0\text{ V}, I_D = 250\text{ }\mu\text{A}$	600	-	-	V	
V_{DS} Temperature Coefficient	$\Delta V_{DS}/T_J$	Reference to $25\text{ }^\circ\text{C}$, $I_D = 1\text{ mA}$	-	660	-	mV/°C	
Gate-Source Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = 250\text{ }\mu\text{A}$	2.0	-	4.0	V	
Gate-Source Leakage	I_{GSS}	$V_{GS} = \pm 30\text{ V}$	-	-	± 100	nA	
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = 600\text{ V}, V_{GS} = 0\text{ V}$	-	-	25	μA	
		$V_{DS} = 480\text{ V}, V_{GS} = 0\text{ V}, T_J = 125\text{ }^\circ\text{C}$	-	-	250		
Drain-Source On-State Resistance	$R_{DS(on)}$	$V_{GS} = 10\text{ V}, I_D = 5.5\text{ A}^b$	-	0.780	-	Ω	
Forward Transconductance	g_{fs}	$V_{DS} = 50\text{ V}, I_D = 5.5\text{ A}$	5.5	-	-	S	
Dynamic							
Input Capacitance	C_{iss}	$V_{GS} = 0\text{ V},$ $V_{DS} = 25\text{ V},$ $f = 1.0\text{ MHz},$ see fig. 5	-	1400	-	pF	
Output Capacitance	C_{oss}		-	180	-		
Reverse Transfer Capacitance	C_{rss}		-	7.1	-		
Output Capacitance	C_{oss}	$V_{GS} = 0\text{ V}$	$V_{DS} = 1.0\text{ V}, f = 1.0\text{ MHz}$	-	1957	-	
Effective Output Capacitance	$C_{oss\text{ eff.}}$		$V_{DS} = 480\text{ V}, f = 1.0\text{ MHz}$	-	49	-	
			$V_{DS} = 0\text{ V to } 480\text{ V}$	-	96	-	
Total Gate Charge	Q_g	$V_{GS} = 10\text{ V}$	$I_D = 8.0\text{ A}, V_{DS} = 400\text{ V}$ see fig. 6 and 13 ^b	-	-	49	nC
Gate-Source Charge	Q_{gs}			-	-	13	
Gate-Drain Charge	Q_{gd}			-	-	20	
Turn-On Delay Time	$t_{d(on)}$	$V_{DD} = 300\text{ V}, I_D = 8.0\text{ A}$ $R_g = 9.1\text{ }\Omega, R_D = 35.5\text{ }\Omega,$ see fig. 10 ^b	-	13	-	ns	
Rise Time	t_r		-	25	-		
Turn-Off Delay Time	$t_{d(off)}$		-	30	-		
Fall Time	t_f		-	22	-		
Gate Input Resistance	R_g		$f = 1\text{ MHz},$ open drain	0.5	-		3.2
Drain-Source Body Diode Characteristics							
Continuous Source-Drain Diode Current	I_S	MOSFET symbol showing the integral reverse p - n junction diode 	-	-	9.2	A	
Pulsed Diode Forward Current ^a	I_{SM}		-	-	37		
Body Diode Voltage	V_{SD}	$T_J = 25\text{ }^\circ\text{C}, I_S = 8.0\text{ A}, V_{GS} = 0\text{ V}^b$	-	-	1.5	V	
Body Diode Reverse Recovery Time	t_{rr}	$T_J = 25\text{ }^\circ\text{C}, I_F = 8.0\text{ A}, di/dt = 100\text{ A}/\mu\text{s}^b$	-	530	800	ns	
Body Diode Reverse Recovery Charge	Q_{rr}		-	3.0	4.4	μC	
Forward Turn-On Time	t_{on}	Intrinsic turn-on time is negligible (turn-on is dominated by L_S and L_D)					

Notes

- Repetitive rating; pulse width limited by maximum junction temperature (see fig. 11).
- Pulse width $\leq 300\text{ }\mu\text{s}$; duty cycle $\leq 2\%$.
- $C_{oss\text{ effective}}$ is a fixed capacitance that gives the same charging time as C_{oss} while V_{DS} is rising from 0 % to 80 % V_{DS} .

TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)

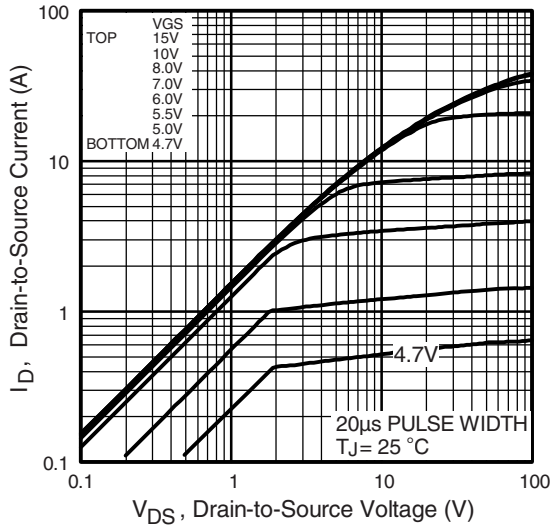


Fig. 1 - Typical Output Characteristics

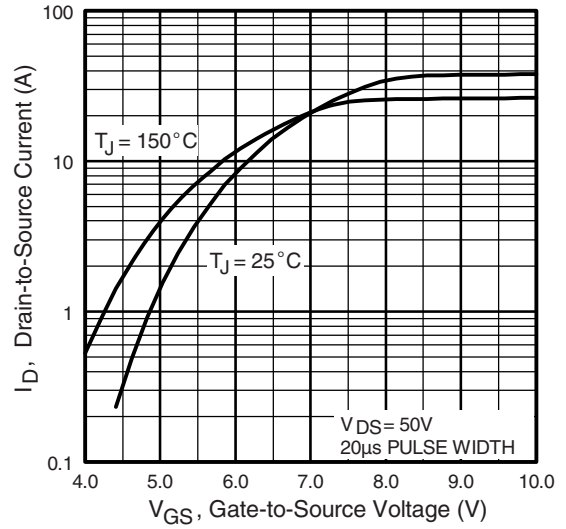


Fig. 3 - Typical Transfer Characteristics

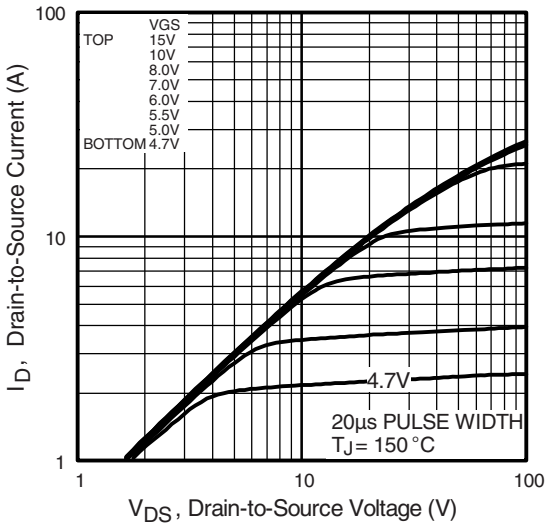


Fig. 2 - Typical Output Characteristics

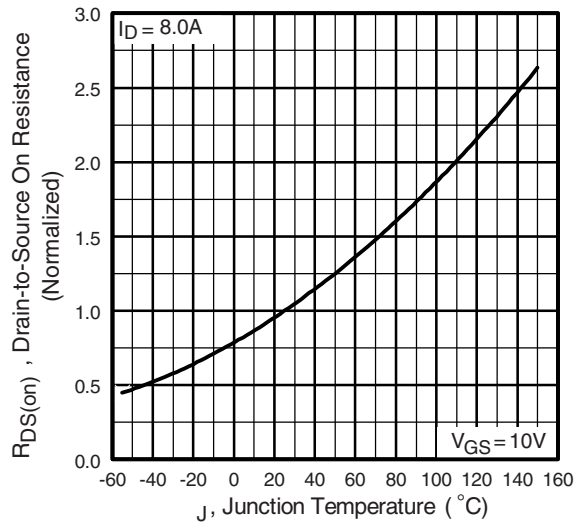


Fig. 4 - Normalized On-Resistance vs. Temperature



Fig. 5 - Typical Capacitance vs. Drain-to-Source Voltage



Fig. 7 - Typical Source-Drain Diode Forward Voltage



Fig. 6 - Typical Gate Charge vs. Gate-to-Source Voltage



Fig. 8 - Maximum Safe Operating Area



Fig. 9 - Maximum Drain Current vs. Case Temperature

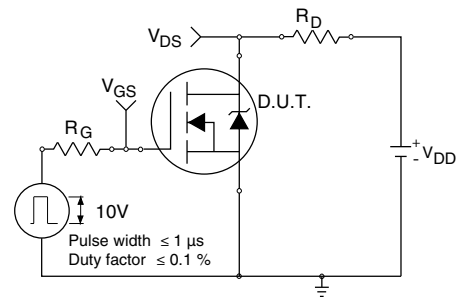


Fig. 10a - Switching Time Test Circuit

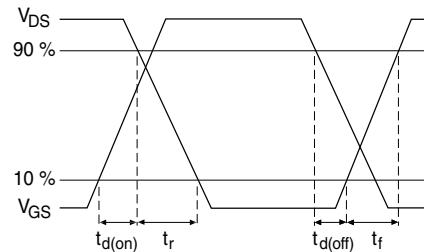


Fig. 10b - Switching Time Waveforms



Fig. 11 - Maximum Effective Transient Thermal Impedance, Junction-to-Case



Fig. 12a - Unclamped Inductive Test Circuit



Fig. 12b - Unclamped Inductive Waveforms

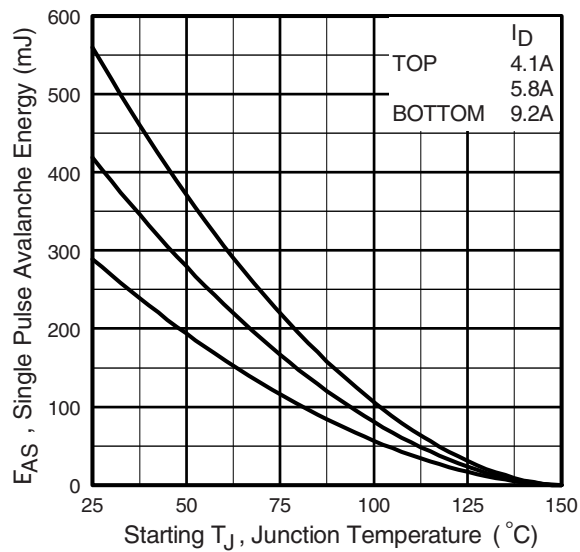


Fig. 12c - Maximum Avalanche Energy vs. Drain Current



Fig. 13a - Basic Gate Charge Waveform



Fig. 13b - Gate Charge Test Circuit

Peak Diode Recovery dV/dt Test Circuit



Note
 a. $V_{GS} = 5 V$ for logic level devices

Fig. 14 - For N-Channel

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